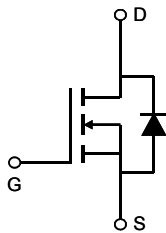
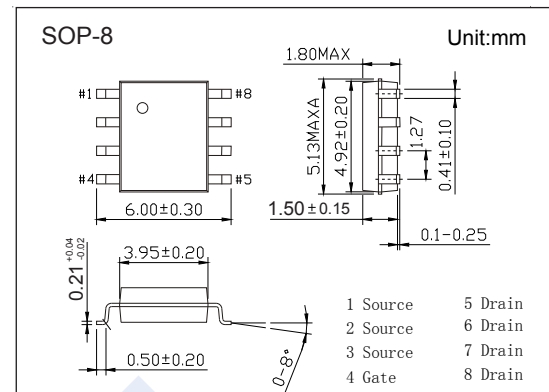


N-Channel MOSFET

AO4486 (KO4486)

■ Features

- $V_{DS} (V) = 100V$
- $I_D = 4.2 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 79m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 90m\Omega (V_{GS} = 4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_A=25^\circ C$	4.2	A
		$T_A=70^\circ C$	3.4	
Pulsed Drain Current	I_{DM}	31		
Avalanche Current	I_{AS}, I_{AR}	14		
Avalanche Energy	$L=0.1mH$	E_{AS}, E_{AR}	10	mJ
Power Dissipation	P_D	$T_A=25^\circ C$	3.1	W
		$T_A=70^\circ C$	2	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40	$^\circ C/W$
		Steady-State	75	
Thermal Resistance.Junction- to-Lead	R_{thJL}	24		
Junction Temperature	T_J	150	$^\circ C$	
Storage Temperature Range	T_{stg}	-55 to 150		

N-Channel MOSFET

AO4486 (KO4486)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.6		2.7	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3A			79	mΩ
		V _{GS} =10V, I _D =3A, T _J =125°C			151	
		V _{GS} =4.5V, I _D =3A			90	
On State Drain Current	I _{D(on)}	V _{GS} =10V, V _{DS} =5V	31			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3A		20		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =50V, f=1MHz	620		942	pF
Output Capacitance	C _{oss}		38		81	
Reverse Transfer Capacitance	C _{rss}		13		35	
Gate Resistance	R _g		0.7		2.2	
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =3A	13		20	nC
Total Gate Charge (4.5V)			6.4		10	
Gate Source Charge	Q _{gs}		2.2		3.4	
Gate Drain Charge	Q _{gd}		2.4		5.8	
Turn-On DelayTime	t _{d(on)}			6		
Turn-On Rise Time	t _r	V _{GS} =10V, V _{DS} =50V, R _L =16.7Ω, R _{GEN} =3Ω	2.5			
Turn-Off DelayTime	t _{d(off)}		21			
Turn-Off Fall Time	t _f		2.4			
Body Diode Reverse Recovery Time	t _{rr}		14		28	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =3A, di/dt=500A/us	65		123	nC
Maximum Body-Diode Continuous Current	I _S				3.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

■ Marking

Marking	4486 KC****
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N-Channel MOSFET AO4486 (KO4486)

■ Typical Characteristics

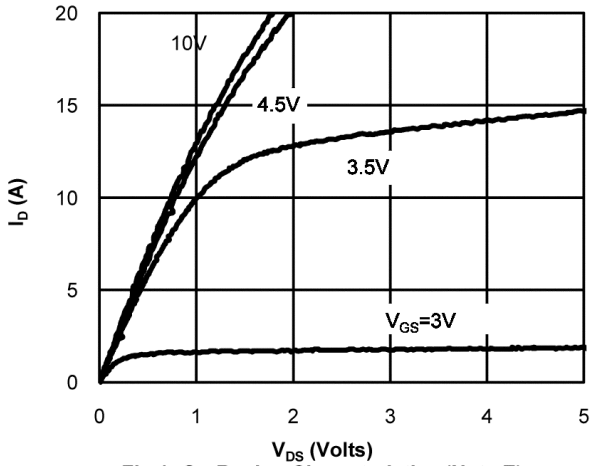


Figure 1: On-Region Characteristics (Note E)

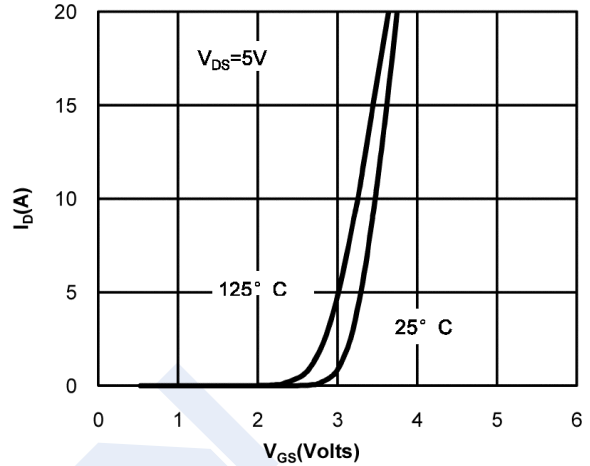


Figure 2: Transfer Characteristics (Note E)

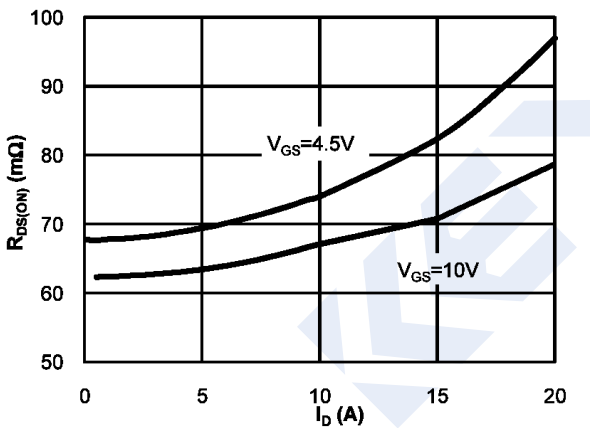


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

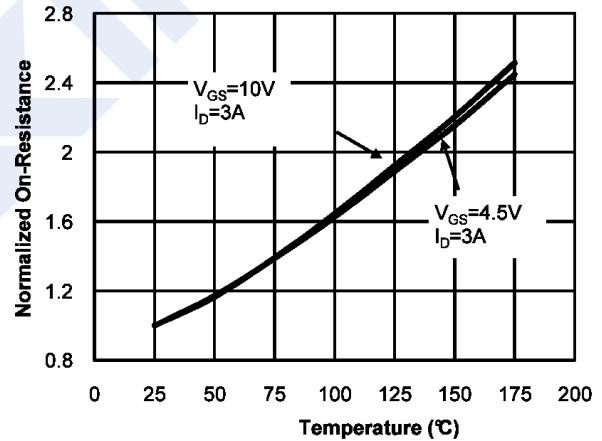


Figure 4: On-Resistance vs. Junction Temperature (Note E)

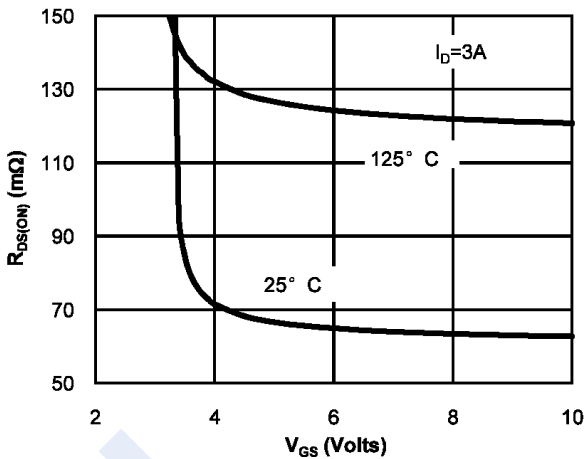


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

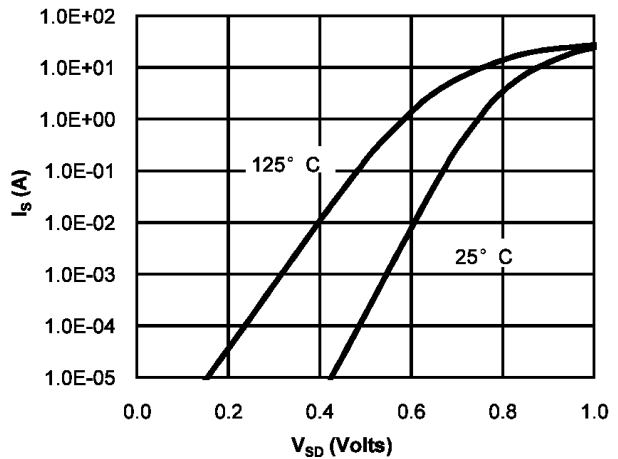


Figure 6: Body-Diode Characteristics (Note E)

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■ Typical Characteristics

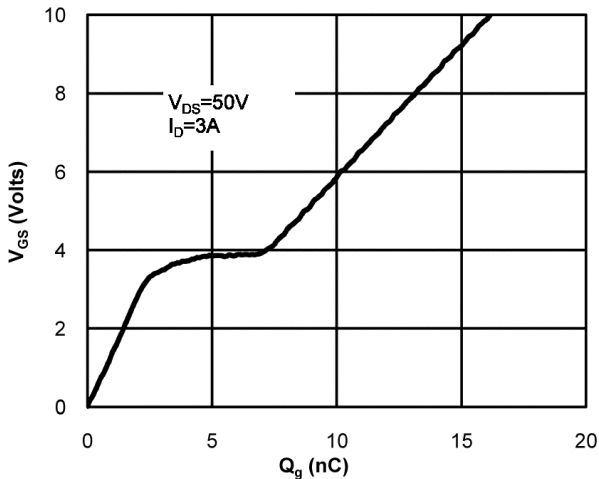


Figure 7: Gate-Charge Characteristics

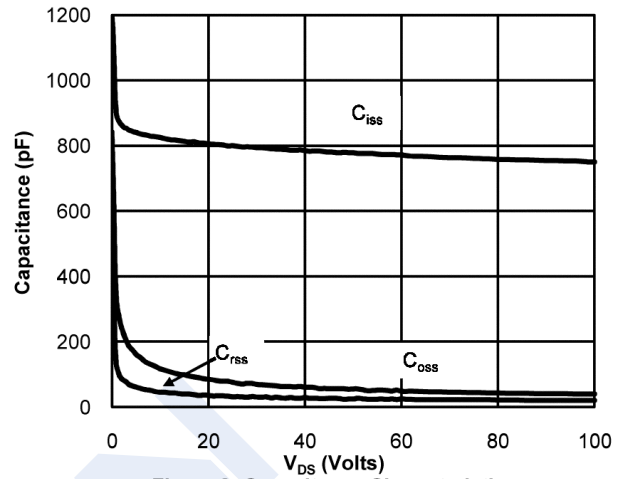


Figure 8: Capacitance Characteristics

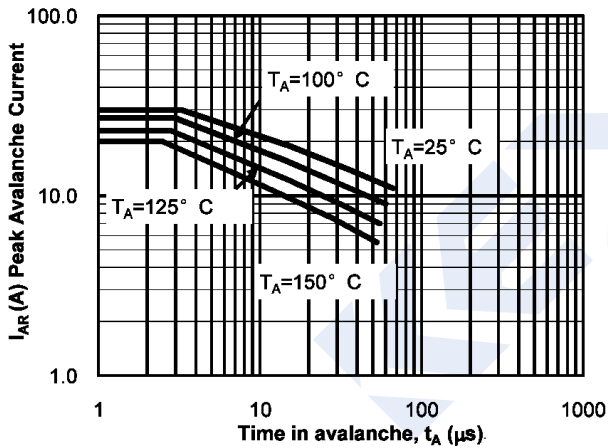


Figure 9: Single Pulse Avalanche capability (Note C)

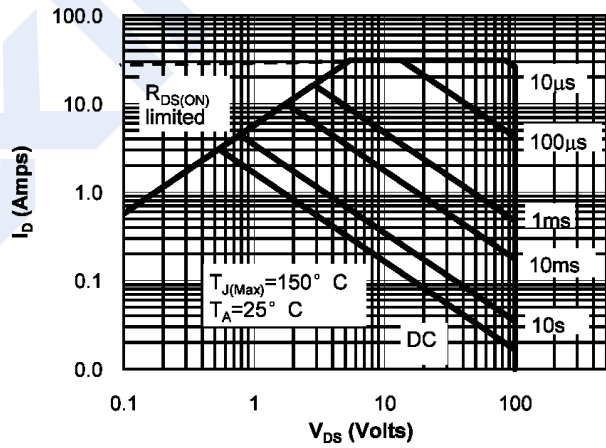


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

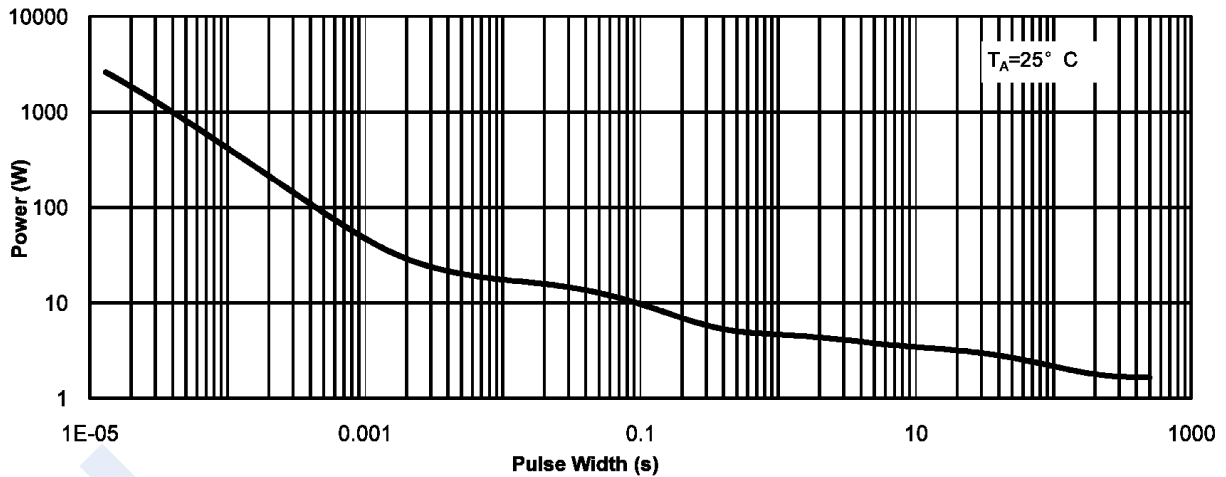


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET AO4486 (KO4486)

■ Typical Characteristics

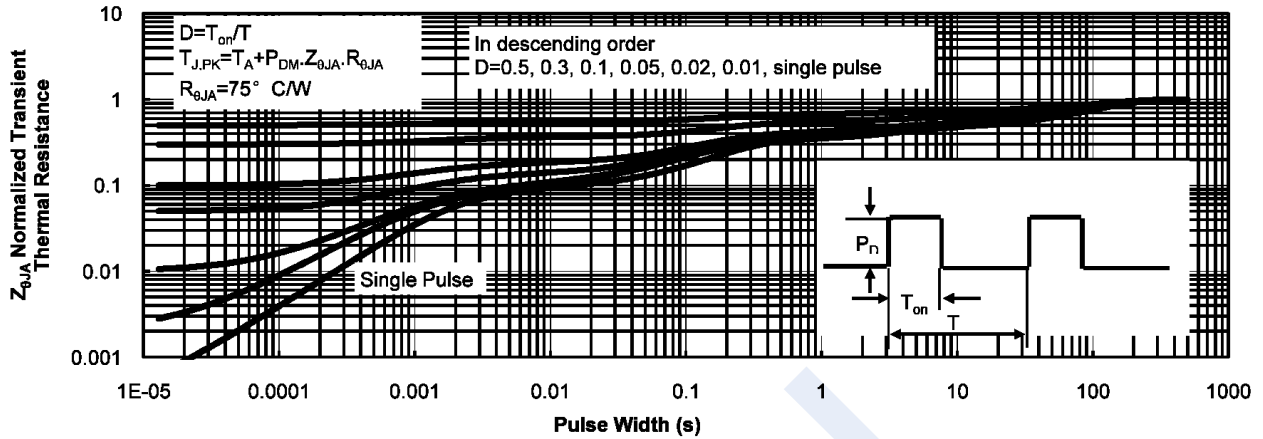


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)